

ZXTAM322

MPPS™ Miniature Package Power Solutions 15V NPN LOW SATURATION TRANSISTOR

SUMMARY

$V_{CE0} = 15V$; $R_{SAT} = 45m\Omega$; $I_C = 4.5A$

DESCRIPTION

Packaged in the innovative 2mm x 2mm MLP (Micro Leaded Package) outline, this new 4th generation low saturation transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

Additionally users will also gain several other **key benefits**:

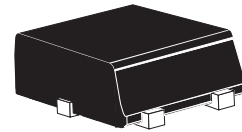
Performance capability equivalent to much larger packages

Improved circuit efficiency & power levels

Lower package height (nom. 0.9mm)

PCB area and device placement savings

Reduced component count



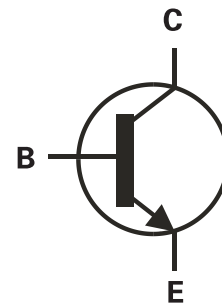
2mm x 2mm MLP
(single die)

FEATURES

- Low Equivalent On Resistance
- Extremely Low Saturation Voltage (**100mVmax @1A**)
- h_{FE} specified up to 12A
- $I_C = 4.5A$ Continuous Collector Current
- 2mm x 2mm MLP

APPLICATIONS

- DC - DC Converters (FET Drivers)
- Charging Circuits
- Power switches
- Motor control



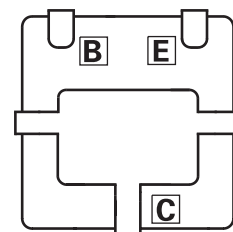
ORDERING INFORMATION

DEVICE	REEL	TAPE WIDTH	QUANTITY PER REEL
ZXTAM322TA	7"	8mm	3000 units
ZXTAM322TC	13"	8mm	10000 units

DEVICE MARKING

SA

PINOUT



2mm x 2mm Single MLP
underside view

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ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	15	V
Emitter-Base Voltage	V_{EBO}	7.5	V
Peak Pulse Current (c)	I_{CM}	15	A
Continuous Collector Current (a)	I_C	4.5	A
Continuous Collector Current (b)	I_C	5	A
Base Current	I_B	1000	mA
Power Dissipation at $T_A=25^\circ\text{C}$ (a) Linear Derating Factor	P_D	1.5 12	W mW/ $^\circ\text{C}$
Power Dissipation at $T_A=25^\circ\text{C}$ (b) Linear Derating Factor	P_D	2.45 19.6	W mW/ $^\circ\text{C}$
Power Dissipation at $T_A=25^\circ\text{C}$ (d) Linear Derating Factor	P_D	1 8	W mW/ $^\circ\text{C}$
Power Dissipation at $T_A=25^\circ\text{C}$ (e) Linear Derating Factor	P_D	3 24	W mW/ $^\circ\text{C}$
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^\circ\text{C}$

THERMAL RESISTANCE

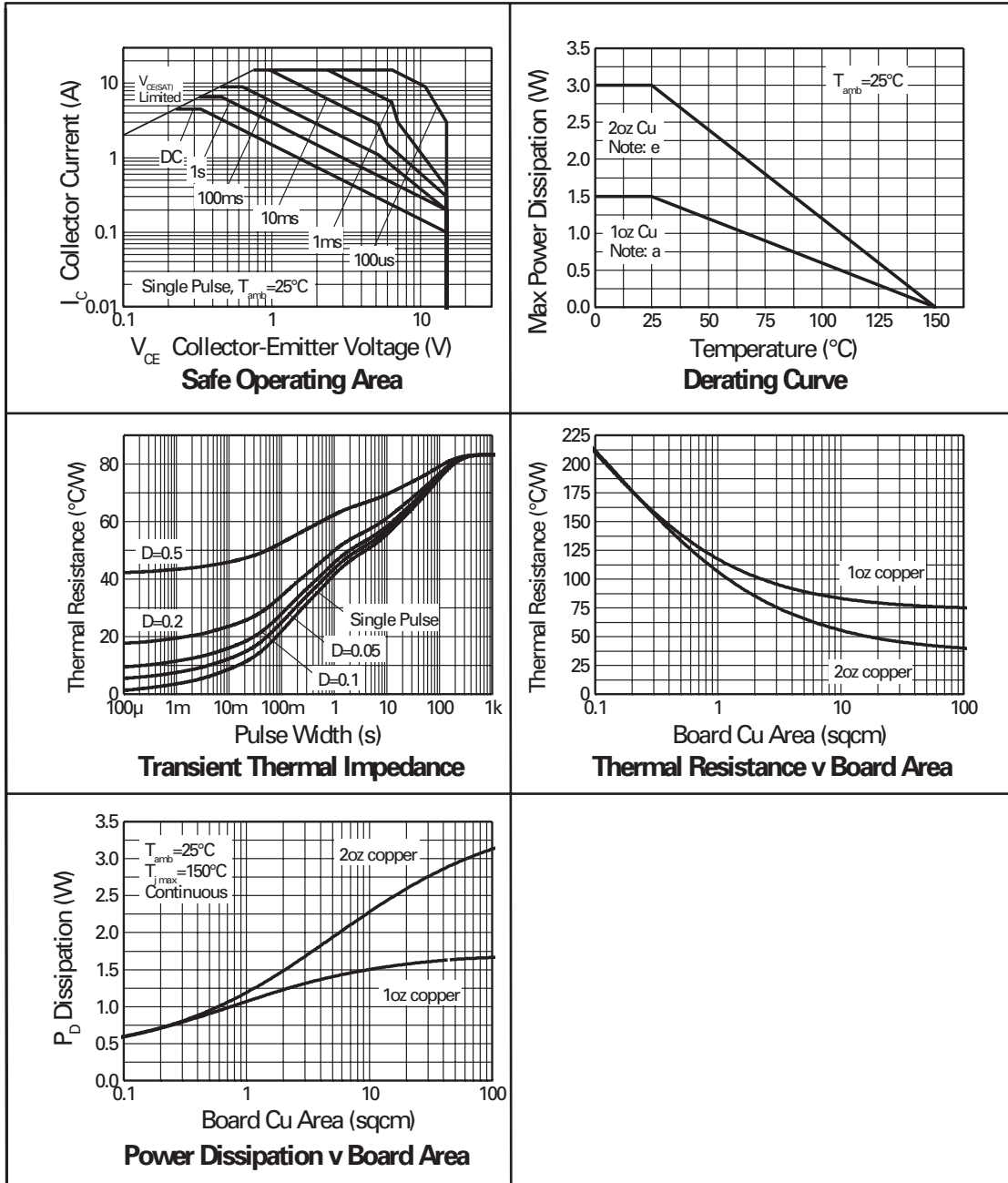
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	83	$^\circ\text{C/W}$
Junction to Ambient (b)	$R_{\theta JA}$	51	$^\circ\text{C/W}$
Junction to Ambient (d)	$R_{\theta JA}$	125	$^\circ\text{C/W}$
Junction to Ambient (e)	$R_{\theta JA}$	42	$^\circ\text{C/W}$

NOTES

- (a) For a single device surface mounted on 10sq cm1oz copper on FR4 PCB in still air conditions **with all exposed pads attached**.
- (b) For a single device surface mounted on 10sq cm1oz copper on FR4 PCB in still air conditions measured at $t \leq 5$ secs **with all exposed pads attached**.
- (c) Repetitive rating - pulse width limited by max junction temperature. refer to Transient Thermal Impedance graph.
- (d) For a single device surface mounted on 10sq cm1oz copper on FR4 PCB in still air conditions **with minimal lead connections only**.
- (e) For a single device surface mounted on 65sq cm2oz copper on FR4 PCB in still air conditions **with all exposed pads attached**.
- (f) The minimum copper dimensions required for mounting are no smaller than the exposed metal pads on the base of the device, as shown in the package dimensions data. The thermal resistance for a device mounted on 1.5mm thick FR4 board using minimum copper of 1oz weight and 1mm wide track is $R_{th}=300^\circ\text{C/W}$ giving a power rating of $P_{tot}=420\text{mW}$.

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TYPICAL CHARACTERISTICS



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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	40	70		V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	15	18		V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	7.5	8.2		V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			25	nA	$V_{CB}=32\text{V}$
Emitter Cut-Off Current	I_{EBO}			25	nA	$V_{EB}=6\text{V}$
Collector Emitter Cut-Off Current	I_{CES}			25	nA	$V_{CES}=12\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		8	14	mV	$I_C=0.1\text{A}, I_B=10\text{mA}^*$
			70	100	mV	$I_C=1\text{A}, I_B=10\text{mA}^*$
			165	200	mV	$I_C=3\text{A}, I_B=50\text{mA}^*$
			240	280	mV	$I_C=4.5\text{A}, I_B=50\text{mA}^*$
			200		mV	$I_C=4.5\text{A}, I_B=100\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		0.94	1.0	V	$I_C=4.5\text{A}, I_B=50\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		0.88	0.95	V	$I_C=4.5\text{A}, V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	200	415			$I_C=10\text{mA}, V_{CE}=2\text{V}^*$
		300	450			$I_C=0.2\text{A}, V_{CE}=2\text{V}^*$
		200	320			$I_C=3\text{A}, V_{CE}=2\text{V}^*$
		150	240			$I_C=5\text{A}, V_{CE}=2\text{V}^*$
			80			$I_C=12\text{A}, V_{CE}=2\text{V}^*$
Transition Frequency	f_T	80	120		MHz	$I_C=50\text{mA}, V_{CE}=10\text{V}$ $f=100\text{MHz}$
Output Capacitance	C_{obo}		30	40	pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Turn-On Time	$t_{(on)}$		120		ns	$V_{CC}=10\text{V}, I_C=1\text{A}$
Turn-Off Time	$t_{(off)}$		160		ns	$I_{B1}=I_{B2}=10\text{mA}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

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TYPICAL CHARACTERISTICS

